NSN 5961-01-107-0970

Thyristor Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

Between 0.170 inches and 0.210 inches

Terminal Length:

Between 0.500 inches and 0.750 inches

Overall Diameter:

Between 0.209 inches and 0.230 inches

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-18

Electrode Internally-electrically Connected To Case:

Gate

Mounting Method:

Terminal

Terminal Circle Diameter:

0.100 inches

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

1.5 forward voltage, peak and 0.8 gate trigger voltage, dc

Current Rating Per Characteristic:

200.00 microamperes forward current, total rms absolute

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnpn

Precious Material And Location:

Terminal surfaces gold

Precious Material:

Gold

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

3 uninsulated wire lead

Specification Data:

81349-mil-s-19500/419 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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